

**ARTICLE COMPRISING GATED FIELD EMISSION STRUCTURES WITH  
CENTRALIZED NANOWIRES AND METHOD FOR MAKING THE SAME**

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**CROSS REFERENCE TO RELATED APPLICATIONS**

This application claims the benefit of the following United States provisional patent applications and is a continuation-in part of the following United States Utility Patent Applications:

1. U.S. Provisional Application Serial No. 60/405,561 filed by S. Jin on August 23, 2002 and entitled "MEMs Based Two-Dimensional E-Beam Nanolithography Device and Method For Making the Same";

2. U.S. Provisional Application Serial No. 60/441,437 filed by S. Jin on January 21, 2003 and entitled "Article Comprising A Gated Field Emission Structure With Centralized Nanowires and Method for Making the Same";

3. U.S. Utility Patent Application Serial No. 10/350,614 filed by S. Jin on January 24, 2003, <sup>PAT 6,909,465</sup> and entitled "Article Comprising MEMs-Based Two Dimensional E-Beam Sources and Method for Making the Same";

4. U.S. Utility Patent Application Serial No. 10/350,642 filed by S. Jin on January 24, 2003 and entitled "MEMs-Based Two Dimensional E-Beam Nano Lithography Device and Method for Making the Same";

5. U.S. Utility Patent Application Serial No. 10/357,004 filed by S. Jin on February 3, 2003 and entitled "Method for Fabricating Spaced-Apart Nanostructures";  
and